

## SPECIFICATION AMENDMENTS

On page 20, please amend the paragraph beginning on line 5, representing the Abstract, as follows:

~~A method for reducing feature size in a thin film magnetic write head using low temperature deposition coating of photolithographically defined trenches. According to the method, a plating seed layer is applied over a selected base layer and a photoresist layer is spun onto the seed layer to a desired thickness. A trench is defined in the photoresist layer to initiate the formation of a stencil for the pole piece. The trench is deep enough to expose the plating seed layer, and has substantially vertical side walls. An insulative spacer layer is deposited to cover the trench side walls using a low temperature chemical vapor deposition process. Horizontal portions of the spacer layer are anisotropically etched to remove spacer layer material from the bottom of the trench and thereby expose the plating seed layer, while leaving intact vertical portions of the spacer layer that cover the trench side walls. This process defines a narrowed trench that is reduced in horizontal size according to approximately twice the thickness of the spacer layer on the trench side walls. A structure of reduced feature size is formed by electroplating metallic material into the narrowed trench. The photoresist layer and the spacer layer vertical portions are then stripped away, and the plating seed layer is milled or sputter etched to leave a structure of reduced feature size.~~

A method for reducing feature size in a thin film magnetic write head includes plating a seed layer over a selected base layer, spinning a photoresist layer onto the seed layer, defining a trench in the photoresist layer, depositing an insulative spacer layer to cover the trench side walls using a low temperature chemical vapor deposition process, anisotropically etching to remove spacer layer material from the bottom of the trench and thereby expose the plating seed layer

while leaving intact vertical portions of the spacer layer that cover the trench side walls and narrow its width, forming a structure of reduced feature size by electroplating metallic material into the narrowed trench, stripping away the photoresist layer and the spacer layer vertical portions, and milling or sputter etching the plating seed layer to leave a structure of reduced feature size.